November 1998

FDS9933A Dual P-Channel 2.5V Specified PowerTrench[™] MOSFET

General Description

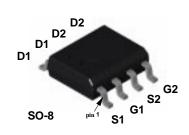
These P-Channel 2.5V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

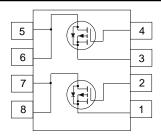
Applications

- Load switch
- DC/DC converter
- Motor drives

Features

- -3.8 A, -20 V. $R_{DS(on)} = 0.075 \ \Omega \ @ V_{GS} = -4.5 \ V$ $R_{DS(on)} = 0.105 \ \Omega \ @ V_{GS} = -2.5 \ V.$
- Low gate charge (7nC typical).
- Fast switching speed.
- High performance trench technology for extremely low R_{DS(on)}.
- High power and current handling capability.





Absolute Maximum Ratings T_=25°C unless otherwise noted

Symbol	Parameter		FDS9933A	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		<u>±</u> 8	V
I _D	Drain Current - Continuous	(Note 1a)	-3.8	А
	- Pulsed		-20	
PD	Power Dissipation for Dual Operation		2.0	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1.0	
		(Note 1c)	0.9	
TJ, Tstg	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R _θ JC	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

Package Marking and Ordering Information

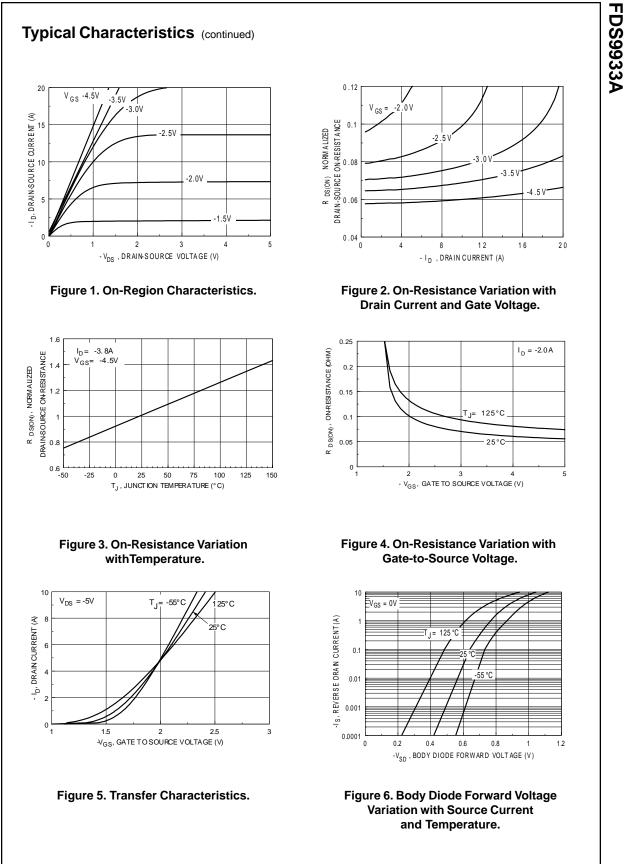
Device Marking	Device	Reel Size	Tape width	Quantity
FDS9933A	FDS9933A	13"	12mm	2500 units

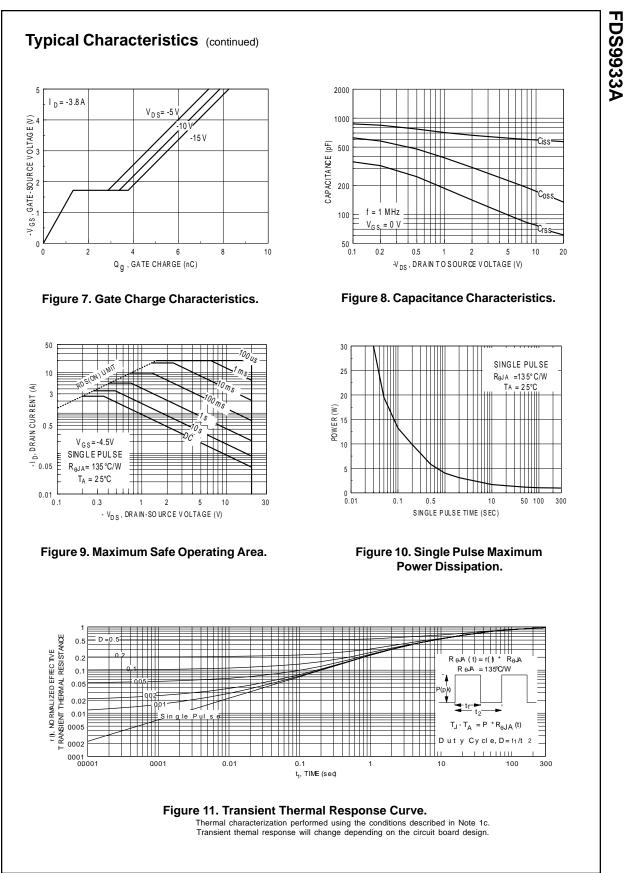
©1998 Fairchild Semiconductor Corporation

Symbol	Parameter	Test Conditions	Min	Тур	Мах	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_D = -250 \mu A$	-20			V
ΔBV dss ΔT_{J}	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$, Referenced to 25°C		-16		mV/∘C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μA
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 8 V, V_{DS} = 0 V$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V_{GS} = -8 V, V_{DS} = 0 V			-100	nA
on Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = -250 \ \mu\text{A}$	-0.4	-0.8	-1.5	V
ΔVGS(th) ΔTJ	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		2.5		mV/∘C
R _{DS(on)}	Static Drain-Source On-Resistance			0.058 0.086 0.084	0.075 0.12 0.105	Ω Ω Ω
D(on)	On-State Drain Current	$V_{GS} = -4.5 \text{ V}, N_{DS} = -5.0 \text{ V}$	-10	0.001	000	A
g FS	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, \text{ I}_{D} = -3.8 \text{ A}$		10		S
ynamic	Characteristics					
viss	Input Capacitance	V_{DS} = -10 V, V_{GS} = 0 V, f = 1.0 MHz		600		pF
oss	Output Capacitance			175		pF
rss	Reverse Transfer Capacitance			80		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = -5 V, I_D = -0.5 A,$		6	12	ns
tr	Turn-On Rise Time	V_{GS} = -4.5 V, R_{GEN} = 6.0 Ω		9	18	ns
t _{d(off)}	Turn-Off Delay Time			31	50	ns
t _f	Turn-Off Fall Time			28	42	ns
Qg	Total Gate Charge	$V_{DS} = -10 V$, $I_{D} = -3.8 A$,		7	10	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -4.5 V		1.3		nC
Q _{gd}	Gate-Drain Charge			2		nC
Drain-Sc	ource Diode Characteristics	and Maximum Ratings				
S	Maximum Continuous Drain-Source	e Diode Forward Current			-1.3	Α
/ _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = -1.3 A$ (Note 2)		-0.75	-1.2	V
	ins. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,JA}$ is	nt resistance where the case thermal reference is of a determined by the user's board design.		⊘ c) 135 ⊖ mou	° C/W whe inted on a of 2 oz. c	n 0.003 in²

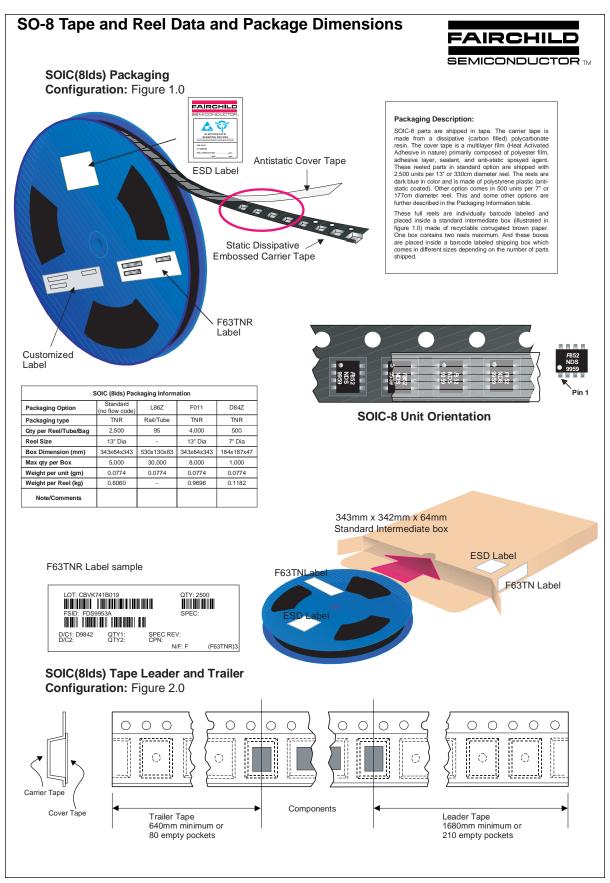
FDS9933A Rev. C

FDS9933A

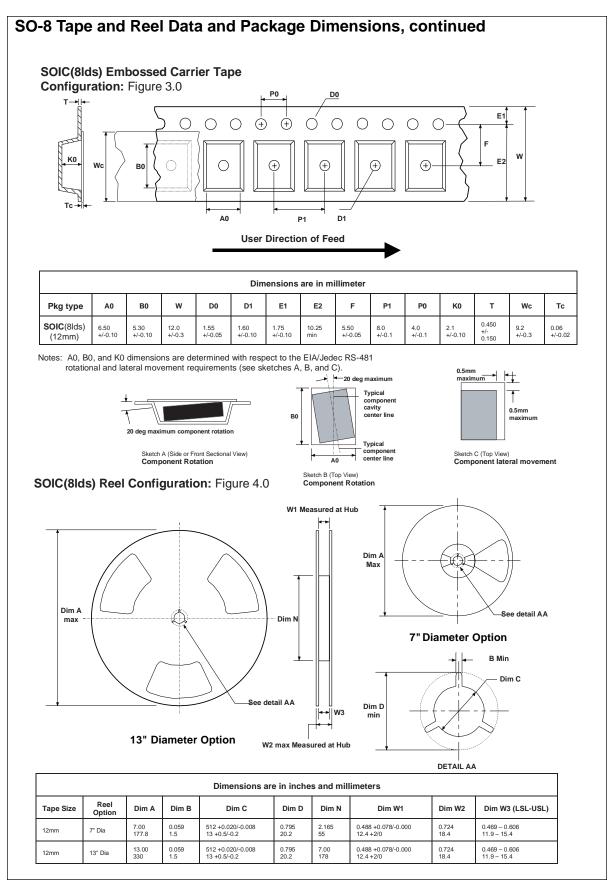


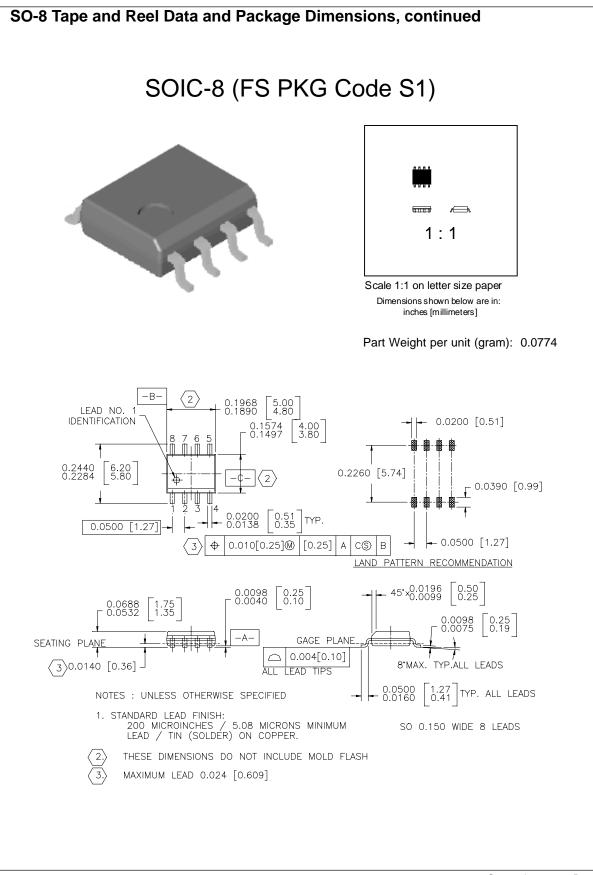


FDS9933A Rev. C



July 1999, Rev. B





TRADEMARKS

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACExTM CoolFETTM CROSSVOLTTM E²CMOSTM FACTTM FACT Quiet SeriesTM FAST[®] FAST[®] FASTrTM GTOTM HiSeCTM ISOPLANAR™ MICROWIRE™ POP™ PowerTrench® QFET™ QS™ Quiet Series™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SyncFET™ TinyLogic™ UHC™ VCX™

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user. 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.